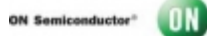
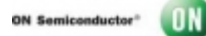
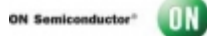


specificazioni	
Numero di parte	FDMS8820
fabbricante	Fairchild/ON Semiconductor
Descrizione	MOSFET N-CH 30V 28A POWER56
Categoria	Prodotti a semiconduttore discreti > Transistor-FET,
Stato parte	10373 pcs Stock
Vgs (th) (max) a Id	2.5V @ 250µA
Vgs (Max)	±20V
Tecnologia	MOSFET (Metal Oxide)
Contenitore dispositivo fornitore	8-PQFN (5x6), Power56
Serie	PowerTrench®
Rds On (max) a Id, Vgs	2 mOhm @ 28A, 10V
Dissipazione di potenza (max)	2.5W (Ta), 78W (Tc)
imballaggio	Tape & Reel (TR)
Contenitore / involucro	8-PowerTDFN
temperatura di esercizio	-55°C ~ 150°C (TJ)
Tipo montaggio	Surface Mount
Capacità di ingresso (Ciss) (Max) @ Vds	5315pF @ 15V
Carica Gate (Qg) (Max) @ Vgs	88nC @ 10V
Tipo FET	N-Channel
Caratteristica FET	-
Tensione dell'azionamento (Max Rds On, Min Rds On)	4.5V, 10V
Tensione drain-source (Vdss)	30V
Corrente - Drain continuo (Id) @ 25 ° C	28A (Ta), 116A (Tc)

 FDMS8880 Fairchild/ON Semiconductor MOSFET N-CH 30V 13.5A POWER56	 FDMS8692 IC FAIRCHILD FAIRCHILD QFN	 FDMS8820 MOS ON ON POWER56-8P	 FDMS8848NZ AMI Semiconductor / ON Semiconductor MOSFET N-CH 40V 22.8A POWER56
 FDMS8692 AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 12A POWER56	 FDMS8692 MOS FAIRCHILD FAIRCHILD QFN	 FDMS8820 AMI Semiconductor / ON Semiconductor MOSFET N-CH 30V 28A POWER56	 FDMS8692S FAIRCHILD FDMS8692S FAIRCHILD

Di Più

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